

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

248145US2S

SERIAL NO. 10/765,031  
New Application

### LIST OF REFERENCES CITED BY APPLICANT

**APPLICANT**

Yoshihisa IWATA, et al.

FILING DATE

Herewith

GROUP

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
NN	AA	6,081,445	06/27/00	Jing SHI, et al.			
NN	AB	6,163,473	12/19/00	Lung T. TRAN			
NN	AC	6,205,051	03/20/01	James A. BRUG, et al.			
	AD						
	AE						
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	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					

**OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)**

NN	AT	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", 2000 IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, ISSCC 2000, DIGEST OF TECHNICAL PAPERS, TD: EMERGING MEMORY & DEVICE TECHNOLOGIES, Session 7, Paper TA 7.2, February 2000, 6 pages	
	AU	M. DURLAM, et al., "Nonvolatile RAM based on Magnetic Tunnel Junction Elements", 2000 IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, ISSCC 2000, DIGEST OF TECHNICAL PAPERS, TD: EMERGING MEMORY & DEVICE TECHNOLOGIES, Session 7, Paper TA 7.3, February 2000, 6 pages	
	AV	Takeshi HONDA, et al., "MRAM-Writing Circuitry to Compensate for Thermal-Variation of Magnetization-Reversal Current", 2002 SYMPOSIUM ON VLSI CIRCUITS DIGEST OF TECHNICAL PAPERS, 12-3, June 2002, 2 pages	
	AW	M. MOTOYOSHI, et al., "High-Performance MRAM Technology with an Improved Magnetic Tunnel Junction Material", 2002 SYMPOSIUM ON VLSI DIGEST OF TECHNICAL PAPERS, 21.4, June 2002, Pages 212-213	
	AX	Manoj BHATTACHARYYA, et al., "Thermal Variations in Switching Fields for Sub-Micron MRAM Cells", IEEE TRANSACTIONS ON MAGNETICS, Vol. 37, No. 4, July 2001, Pages 1970-1972	
	AY	Ricardo C. SOUSA, et al., "Dynamic Switching of Tunnel Junction MRAM Cell with Nanosecond Field Pulses", IEEE TRANSACTIONS ON MAGNETICS, Vol. 36, No. 5, September 2000, Pages 2770-2772	
fN	AZ	Paul R. GRAY, et al., "Analysis and Design of Analog Integrated Circuits-2 <sup>nd</sup> Edition" Japanese Edition, 1 <sup>st</sup> Y. IWATA Volume, Pages 270-276	<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



**LIST OF RELATED CASES**

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>	<u>Client's Reference Number</u>
248145US2S*	10/765,131	01/28/04	IWATA et al.	ACG035274-USA-A T1NK-02S1435
251023US2S	10/807,454	03/24/04	IWATA et al.	ACG036525-USA-A T1HS-03S1460

Considered 9/13/05

Nam Nguyen



**LIST OF RELATED CASES**

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>
248145US2S*	10/765,131	01/28/04	IWATA et al.
255901US2S	10/890,455	07/14/04	IWATA

Considered 3/13/05  
Nam Nguyen



**LIST OF RELATED CASES**

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Patent Appl. Publication No.</u>	<u>Inventor/ Applicant</u>
248145US2S*	10/765,131	01/28/04	2004-0252551	IWATA et al.
264846US2S	11/037,108	01/19/05		IWATA

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Nam Nguyen

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<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>
237768US2S	10/438,015	05/15/03	IWATA et al.

Considered 9/13/05  
Nam Nguyen